<u>TOSHIBA</u>

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

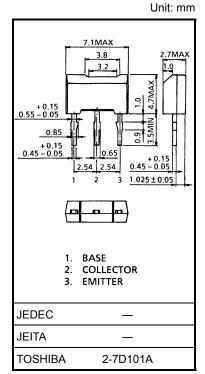
2SA1430

Strobe Flash Applications Medium Power Amplifier Applications

- High DC current gain and excellent hFE linearity
 hFE (1) = 140 to 600 (V_{CE} = -1 V, I_C = -0.5 A)
 hFE (2) = 60 (min), 120 (typ.) (V_{CE} = -1 V, I_C = -4 A)
- Low saturation voltage: V_{CE} (sat) = -0.5 V (max) (I_C = -2 A, I_B = -50 mA)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-20	V	
Collector-emitter voltage		V _{CES}	-20	V	
		V _{CEO}	-10		
Emitter-base voltage		V _{EBO}	-6	V	
Collector current	DC	IC	-2	A	
	Pulsed (Note 1)	I _{CP}	-4		
Base current		Ι _Β	-2	А	
Collector power dissipation		P _C	1000	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 0.2 g (typ.)

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

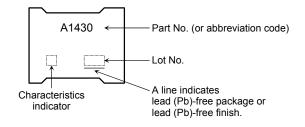
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

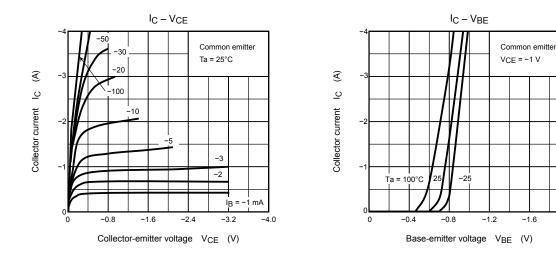
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -20 V, I_E = 0$	_	_	-100	nA
Emitter cut-off current	I _{EBO}	$V_{EB} = -6 V, I_C = 0$	_	-	-100	nA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = -10 mA, I _B = 0	-10	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_{\rm E} = -1 {\rm mA}, I_{\rm C} = 0$	-6	_	_	V
DC current gain	h _{FE (1)} (Note 3)	V _{CE} = -1 V, I _C = -0.5 A	140	_	600	
	h _{FE (2)}	V _{CE} = -1 V, I _C = -4 A	60	120	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -2 A, I _B = -50 mA	_	-0.20	-0.50	V
Base-emitter voltage	V _{BE}	V _{CE} = -1 V, I _C = -2 A	_	-0.83	-1.5	V
Transition frequency	fT	V _{CE} = -1 V, I _C = -0.5 A	_	140	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	—	50	_	pF

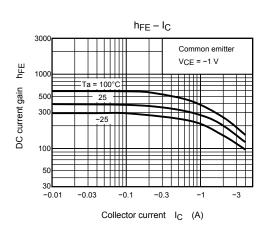
Note 3: hFE (1) classification A: 140 to 280, B: 200 to 400, C: 300 to 600

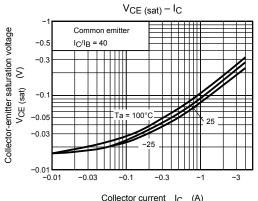
Marking

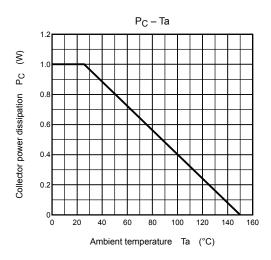


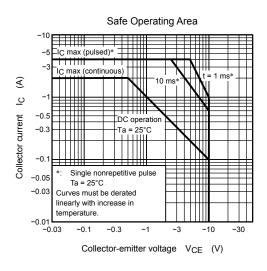
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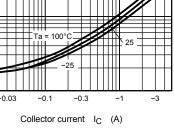












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